

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14650	source and gate and drain and organic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:06
L2	12553	I1 and (under etch\$ or undercut)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:07
L3	7022	I2 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:07
L4	6462	I3 and oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:08
L5	3048	I4 and (H or OH)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:08
L6	2713	I5 and etch\$	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:09
L7	2654	I6 and silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:09
L8	1131	I7 and molecule	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 08:16